

Silicon NPN Power Transistors 2N5606 2N5608 2N5610 2N5612

DESCRIPTION

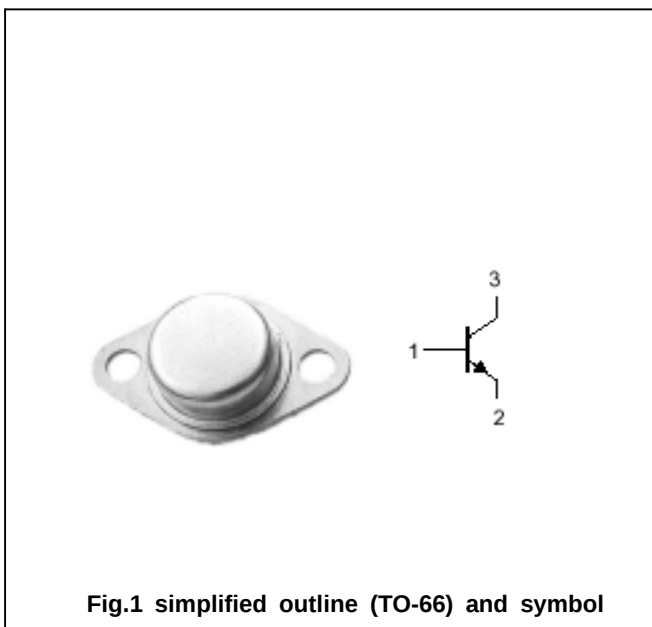
- With TO-66 package
- Excellent safe operating area
- Low collector-emitter saturation voltage

APPLICATIONS

- For general-purpose amplifier ;
and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5606	Open emitter	60	V
		2N5608/5610		80	
		2N5612		100	
V_{CEO}	Collector-emitter voltage	2N5606	Open base	80	V
		2N5608/5610		100	
		2N5612		120	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			5	A
P_D	Total power dissipation		$T_C = 25$	25	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	4.37	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter sustaining voltage	2N5606	I _C =50mA ; I _B =0	60			V
		2N5608/5610		80			
		2N5612		100			
V _{CEsat}	Collector-emitter saturation voltage		I _C =1A; I _B =0.1A			0.5	V
V _{BE}	Base-emitter on voltage		I _C =2.5A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =Rated V _{CBO} ; I _E =0			0.1	mA
I _{CEO}	Collector cut-off current		V _{CE} = Rated V _{CEO} , I _B =0			1.0	mA
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	2N5606/5610	I _C =2.5A ; V _{CE} =5V	70		200	
		2N5608/5612		30		90	
f _T	Transition frequency	2N5606/5610	I _C =0.5A ; V _{CE} =10V	70			MHz
		2N5608/5612		60			

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PACKAGE OUTLINE

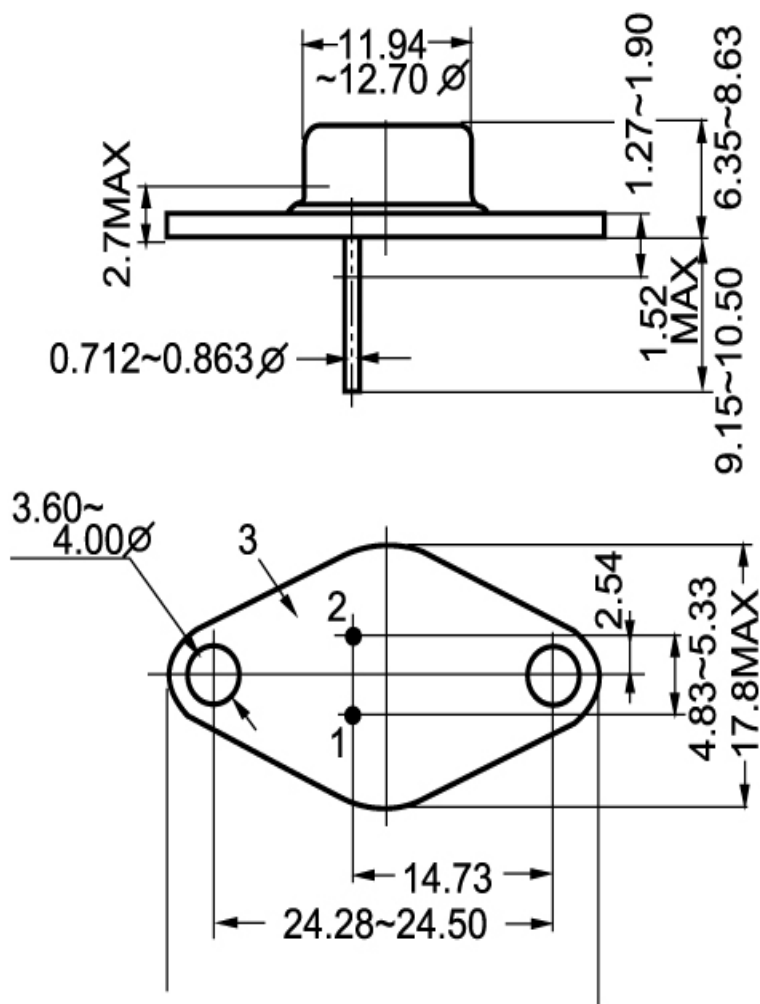


Fig.2 outline dimensions